	77.1	Garage Mout	DB	Time stamp
L Number	Hits	Search Text wafer with chamber with cooling	USPAT;	2002/09/30 13:44
1	670	water with chamber with cooring	EPO; JPO	
-	23	(wafer with chamber with cooling) with	USPAT;	2002/09/30 13:45
5	23	((reactant reactive source) adj3 gas\$2)	EPO; JPO	
	200700	argon helium nitrogen	USPAT	2002/09/27 13:47
-	388700 970227	oxygen ammonia TaETO "nitrogen monoxide"	USPAT	2002/03/02 16:26
-	9/022/	"Nitrogen oxide" "Mononitrogen" monoxide	001	
		"Nitric oxide"	1	
		"Nitrous Oxide"		
		"dinitrogen monoxide" "hyponitrous acid"		
		"anhydride Nitrogen Oxide" "Dinitrogen	1	
		oxide"		
		0.1243		
		"dihydrogen oxide" "Hydrogen oxide" Water		
-	330656	(argon helium nitrogen) and (oxygen	USPAT	2002/03/02 16:26
		ammonia TaETO "nitrogen monoxide"		
		"Nitrogen oxide" "Mononitrogen" monoxide		
		"Nitric oxide"		
		"Nitrous Oxide"		
		"dinitrogen monoxide" "hyponitrous acid"		
		"anhydride Nitrogen Oxide" "Dinitrogen		
		oxide"		
		Halbudanan aridal "Hudnogon oyido" Nator		
	•	"dihydrogen oxide" "Hydrogen oxide" Water		
	2983	((argon helium nitrogen) and (oxygen	USPAT	2002/03/02 16:27
] -	2903	ammonia TaETO "nitrogen monoxide"	00000	
		"Nitrogen oxide" "Mononitrogen" monoxide		
		"Nitric oxide"		
		"Nitrous Oxide"		
		"dinitrogen monoxide" "hyponitrous acid"		
		"anhydride Nitrogen Oxide" "Dinitrogen		
		oxide"		
1		name and a second		
		"dihydrogen oxide" "Hydrogen oxide" Water		
)) and "vacuum pressure"	USPAT	2002/03/02 16:35
-	2983	(((argon helium nitrogen) and (oxygen ammonia TaETO "nitrogen monoxide"	USFAI	2002/03/02 10.33
		"Nitrogen oxide" "Mononitrogen" monoxide		
	1	"Nitric oxide"		
		"Nitrous Oxide"		
		"dinitrogen monoxide" "hyponitrous acid"		
1		"anhydride Nitrogen Oxide" "Dinitrogen	1	
		oxide"		
		"dihydrogen oxide" "Hydrogen oxide" Water		
	1)) and "vacuum pressure") and vacuum		0000/00/00 10 55
-	13		USPAT	2002/03/02 16:28
		ammonia TaETO "nitrogen monoxide"		
		"Nitrogen oxide" "Mononitrogen" monoxide		
	1	"Nitric oxide" "Nitrous Oxide"	-	
		"dinitrogen monoxide" "hyponitrous acid"		
		"anhydride Nitrogen Oxide" "Dinitrogen	1	
		oxide"		
		"dihydrogen oxide" "Hydrogen oxide" Water		
1)) and "vacuum pressure") and vacuum) and		
	<u> </u>	(dilut\$3 near nitrogen)	<u></u>	

	T25000			10000/02/06 55 55
_	535039	((((argon helium nitrogen) and (oxygen ammonia TaETO "nitrogen monoxide"	USPAT	2002/03/02 16:33
		"Nitrogen oxide" "Mononitrogen" monoxide		
		"Nitric oxide"		
		"Nitrous Oxide"		
		"dinitrogen monoxide" "hyponitrous acid" "anhydride Nitrogen Oxide" "Dinitrogen		
	j	oxide"		
		Wdibudaaan anidal Wudaaan anidal Water		
		"dihydrogen oxide" "Hydrogen oxide" Water)) and "vacuum pressure") and vacuum) and		
		ultra thin		
-	354	(())	USPAT	2002/03/02 16:34
		ammonia TaETO "nitrogen monoxide" "Nitrogen oxide" "Mononitrogen" monoxide		
		"Nitric oxide"		
:		"Nitrous Oxide" "dinitrogen monoxide" "hyponitrous acid"		
		"anhydride Nitrogen Oxide" "Dinitrogen		
		oxide"		
		"dihydrogen oxide" "Hydrogen oxide" Water		
)) and "vacuum pressure") and vacuum and		
_	59	ultra	Hanne	0000/02/02 15 55
_	39	(((argon helium nitrogen) and (oxygen ammonia TaETO "nitrogen monoxide"	USPAT	2002/03/02 16:35
		"Nitrogen oxide" "Mononitrogen" monoxide		
		"Nitric oxide" "Nitrous Oxide"		
		"dinitrogen monoxide" "hyponitrous acid"		
		"anhydride Nitrogen Oxide" "Dinitrogen		
		oxide"		
		"dihydrogen oxide" "Hydrogen oxide" Water		
)) and "vacuum pressure") and vacuum and LPCVD]	
_	57		USPAT	2002/03/02 16:35
		ammonia TaETO "nitrogen monoxide"		
		"Nitrogen oxide" "Mononitrogen" monoxide "Nitric oxide"		
		"Nitrous Oxide"		
		"dinitrogen monoxide" "hyponitrous acid"		
		"anhydride Nitrogen Oxide" "Dinitrogen oxide"		
		H4/24		
		"dihydrogen oxide" "Hydrogen oxide" Water)) and "vacuum pressure") and vacuum and		
		LPCVD) and temperature		
-	2149	unload\$3 near (wafer substrate	USPAT;	2002/09/27 13:50
		semiconductor)	US-PGPUB; EPO; JPO	
-	1148	(unload\$3 near (wafer substrate	USPAT;	2002/09/27 13:51
		semiconductor)) and temperature	US-PGPUB;	
-	50	((unload\$3 near (wafer substrate	EPO; JPO USPAT;	2002/09/27 15:02
		semiconductor)) and temperature) and	US-PGPUB;	
_	308	((steady adj3 state) "steady state") cluster adj2 tools	EPO; JPO USPAT;	2002/09/27 15:03
			US-PGPUB;	2002/03/27 13.03
_	120	(cluster adj2 tools) and cooling	EPO; JPO	2002/00/27 15-25
	120	(orabler dajz coors) and coorring	USPAT; US-PGPUB;	2002/09/27 15:25
_	175	hondoway us	EPO; JPO	0000/05/05
-	175	bonderer.xa.	USPAT; US-PGPUB;	2002/09/27 15:26
			EPO; JPO	•
-	157	kilday.xa.	USPAT;	2002/09/27 15:42
			US-PGPUB; EPO; JPO	
			7.01 0.0	

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